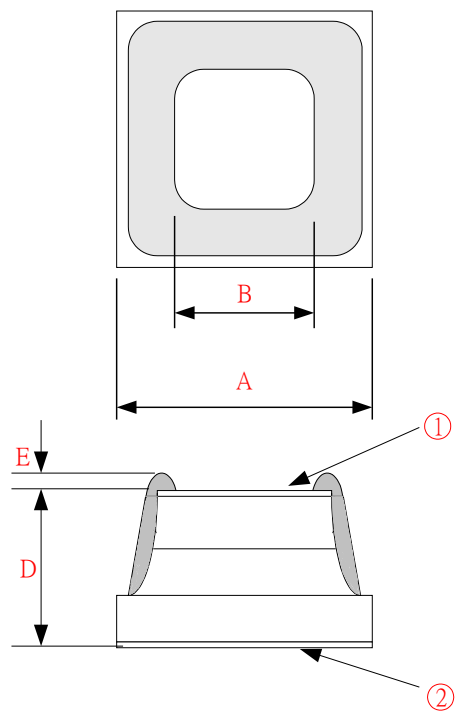


| Product | Type | | | | | | | | | | |
|--|--------------------|-----------|---|-------|---|-----------|---|--------|---|--------|--|
| Ultra Fast Rectifier Diodes Top Al ① Bottom Ag ② | GPWH75610-4-02-3RD | | | | | | | | | | |
| Metallization Dimension in mils <table border="1" data-bbox="70 473 566 782"> <thead> <tr> <th></th> <th>Dimension</th> </tr> </thead> <tbody> <tr> <td>A</td> <td>298±2</td> </tr> <tr> <td>B</td> <td>270(min.)</td> </tr> <tr> <td>D</td> <td>10.5±1</td> </tr> <tr> <td>E</td> <td>1.5.±1</td> </tr> </tbody> </table> | | Dimension | A | 298±2 | B | 270(min.) | D | 10.5±1 | E | 1.5.±1 |  <p>The drawing shows a square package with a central square opening. Dimension A is the total width, B is the width of the central opening, D is the height of the package, and E is the thickness of the top layer. Callout 1 points to the top metal layer, and callout 2 points to the bottom metal layer.</p> |
| | Dimension | | | | | | | | | | |
| A | 298±2 | | | | | | | | | | |
| B | 270(min.) | | | | | | | | | | |
| D | 10.5±1 | | | | | | | | | | |
| E | 1.5.±1 | | | | | | | | | | |

Absolute Maximum Ratings (Ta=25°C)

PEAK REVERSE VOLTAGE VRM .. 1000 V

FORWARD SURGE CURRENT IFSM...600 A

STORAGE TEMPERATURE RANGE Tstg .. -65~150°C

Electrical Characteristics

| Item | Symbol | Test Condition | Standard |
|--------------------------------|--------|----------------|--------------|
| FORWARD VOLTAGE(for cell type) | VF | IF=70A | 1.85 V (MAX) |
| REVERSE CURRENT | IR | VR=1000V | 10μA (MAX) |
| REVERSE RECOVERY TIME | TRR | RG1 | 90ns |
| BREAKDOWN VOLTAGE | BVR | IR=10μA | 1020V (MIN) |

Quality Yield Assurance per wafer: 70%

| | | |
|---------------------------|-------------------------|--------------------|
| Ho Chien Electronics Inc. | Spec No. GPWH75610-4-01 | DATE : Sep.22.2006 |
|---------------------------|-------------------------|--------------------|